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EUROPEAN PATENT OF CE

Patent Abstracts of Japan

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APPLICANT:

OLYMPUS OPTICAL CO LTD;

INVENTOR:

KAWAMATA TAKESHI;

INT.CL.

G02B 1/10 C30B 25/06

TITLE

PRODUCTION OF OPTICAL THIN FILM

ABSTRACT :

PURPOSE: To produce an optical thin film of high quality at a low cost by using a single

crystal Si target to produce the thin film.

CONSTITUTION: In the production process of an optical thin film, a single crystal Si target is used to form a SiO $_2$ film by reactive sputtering in the environment into which at least two kinds of gases of a gas containing oxygen and an inert gas are introduced while impressing pulses of positive voltage on a DC power source. In this method, the resistance of the single crystal Si target is specified to $\leq 10 m\Omega$.cm. By this method, since no intergranular interface is present in the crystal different from a polycrystalline target, the surface roughness of the target is not increased. Therefore, arc discharge is hardly caused. The target has excellent uniformity in the target surface, and as a result, even when a film is formed on a large substrate, the film quality shows higher uniformity. By impressing pulses of positive voltage on the DC power source, charges hardly accumulate on the surface of the target.

on the surface of the target.

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